



AC847BQ-AC847CQ-AC848BQ

NPN SMALL SIGNAL TRANSISTOR IN SOT23

Description

The bipolar junction transistors (BJT) are designed to meet the stringent requirements of automotive applications.

Features

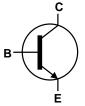
- Ideally Suited for Automatic Insertion
- Complementary PNP Types: AC857BQ AC857CQ AC858BQ
- For Switching and AF Amplifier Applications
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

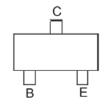
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.008 grams (Approximate)









Top View

Device Symbol

Top View Pin-Out

Ordering Information (Notes 4 & 5)

Product	Compliance	Marking	Reel Size (inches)	Quantity per Reel
AC847BQ-7	Automotive	2D1	7	3000
AC847CQ-7	Automotive	2C9	7	3000
AC848BQ-7	Automotive	2K9	7	3000
AC848BQ-13	Automotive	2K9	13	10,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + CI) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.
- 5. For packaging details, see https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



XXX = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: G = 2019) M or \overline{M} = Month (ex: 9 = September)

Date Code Key

Year	2017	2018	2019	2020	2021	2022	2023	2024	2025	2026	2027	2028
Code	Е	F	G	Н	ı	J	K	L	М	N	0	Р
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Collector-Base Voltage	AC847	V	50	V
Collector-base voltage	AC848	V _{СВО}	30	V
Callactor Emitter Valtage	AC847	V	45	V
Collector-Emitter Voltage	AC848	V _{CEO}	30	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \
Emitter Base Voltage	AC847	V	6.0	V
Emitter-Base Voltage	AC848	V _{EBO}	5.0	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \
Continuous Collector Current	Ic	100	mA	
Peak Collector Current	I _{CM}	200	mA	
Peak Emitter Current		I _{EM}	200	mA

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 6)	D	310	mW
Power Dissipation	(Note 7)	P _D	350	IIIVV
Thermal Resistance, Junction to Ambient	(Note 6)	D	403	°C/W
Thermal Resistance, Junction to Ambient	(Note 7)	R _{OJA}	357	C/VV
Thermal Resistance, Junction to Leads (Note 8)		R _{ÐJL}	350	°C/W
Operating and Storage Temperature Range	$T_{J,}T_{STG}$	-65 to +150	°C	

ESD Ratings (Note 9)

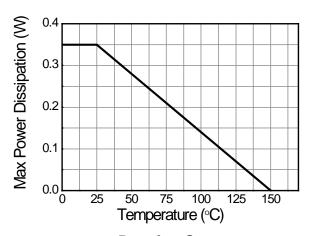
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge—Human Body Model	ESD HBM	4000	V	3A
Electrostatic Discharge—Machine Model	ESD MM	400	V	С

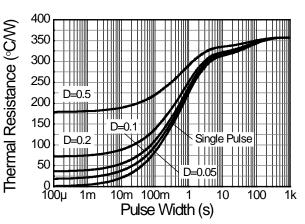
Notes:

- 6. For a device mounted on minimum recommended pad layout 1oz copper that is on a single-sided FR-4 PCB; device is measured under still air 6. For a device mounted on minimum recommended pad layout 102 copper that is conditions whilst operating in a steady-state.
 7. Same as Note 6 except the device is mounted on 15mm x 15mm 1oz copper.
 8. Thermal resistance from junction to solder-point (at the end of the leads).
 9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



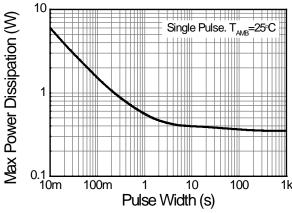
Thermal Characteristics and Derating Information





Derating Curve

Transient Thermal Impedance



Pulse Power Dissipation



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Min	Тур	Max	Unit	Test Condition	
Collector-Base Breakdown Voltage		AC847	BV _{CBO}	50	_	_	V	$I_C = 10\mu A$	
Policotor Base Breakdown Voltage		AC848	DVCBO	30	_	_	_	_	
Collector-Emitter Breakdown Voltage (Note 10) AC847 AC848		AC847	BV _{CEO}	45	_	_	V	$I_C = 10mA$	
		DACEO	30	_	_		_		
Emitter-Base Breakdown Voltage AC847		AC847	BV _{EBO}	6	_	_	V	$I_E = 1\mu A$	
Emilier Base Breakdown Voltage		AC848	PAERO	5	_			_	
Collector Cutoff Current			1			15	nA	$V_{CB} = 30V$	
Collector Cutoff Current			I _{CBO}		_	5	μΑ	$V_{CB} = 30V, T_J = +150$ °C	
Collector Emitter Cutoff Current			ICES	_	_	15	nA	V _{CE} = 50V	
Emitter Base Cutoff Current			I _{EBO}	_	_	100	nA	V _{EB} = 5V	
Small Signal Current Gain (Note 10)	AC84	7BQ/AC848BQ	-		330				
Small Signal Current Gain (Note 10)		AC847CQ	h _{fe}		600		_		
Input Impedance (Note 10)		7BQ/AC848BQ	h _{ie}		4.5		kΩ		
imput impedance (Note 10)		AC847CQ	He		8.7			$I_C = 2.0 \text{mA}, V_{CE} = 5 \text{V}$ f=1.0kHz	
Output Admittance (Note 10)		7BQ/AC848BQ	hoe	_	30	_	μs		
		AC847CQ	1.06		60				
Reverse Voltage Transfer Ratio (Note 10)		7BQ/AC848BQ	h _{re}	_	2x10 ⁻⁴	_	_		
Therefore Tellage Trailers Thaile (Field Tel)		AC847CQ	1116		3x10 ⁻⁴				
DC Current Gain (Note 10)		7BQ/AC848BQ	her l	200	290	450	_	$I_{C} = 2.0 \text{mA}, V_{CE} = 5 \text{V}$	
Do Garroni Garri (11010-10)		AC847CQ	'''	420	520	800			
Collector-Emitter Saturation Voltage (Note	10)		V _{CE(SAT)}	_	90	250	mV	$I_C = 10mA, I_B = 0.5mA$	
Concotor Emilion Cataration Voltage (Note	10)		V CE(SAT)		200	600		$I_C = 100 \text{mA}, I_B = 5.0 \text{mA}$	
Base-Emitter Turn-On Voltage (Note 10)			V-=	580	660	700	mV	$I_C = 2mA$, $V_{CE} = 5V$	
Base-Emilier Funi-On Voltage (Note 10)			V _{BE(ON)}	_	_	770	IIIV	$I_C = 10mA, V_{CE} = 5V$	
Base-Emitter Saturation Voltage (Note 10)			.,		700		mV	$I_C = 10mA, I_B = 0.5mA$	
Base-Efficier Saturation voltage (Note 10)			$V_{BE(SAT)}$) —	900	_	mv	$I_C = 100 \text{mA}, I_B = 5 \text{mA}$	
Output Capacitance			C _{OBO}		3	_	pF	V _{CB} = 10V, f = 1.0MHz	
Transition Frequency			f⊤	100	300		MHz	V _{CE} = 5V, I _C = 10mA, f = 100MHz	
Noise Figure			NF	_	2	10	dB	V_{CE} =5V, I_{C} =200μA R_{S} =2k Ω , f=1kHz Δ f=200Hz	

Note:

10. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

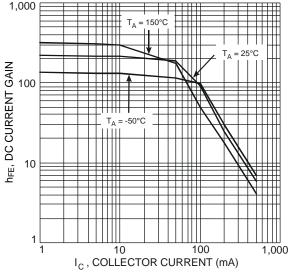


Figure 1 Typical DC Current Gain vs. Collector Current

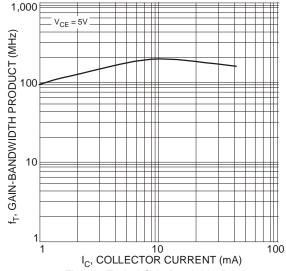


Figure 3 Typical Gain-Bandwidth Product vs. Collector Current

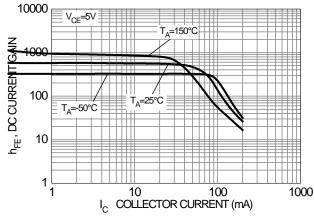


Figure 5 Typical DC Current Gain vs. Collector Current (Band C Group Gain)

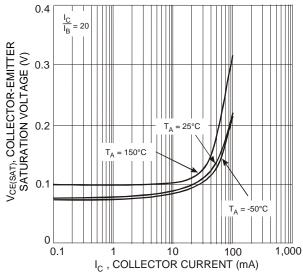


Figure 2 Typical Collector-Emitter Saturation Voltage vs. Collector Current

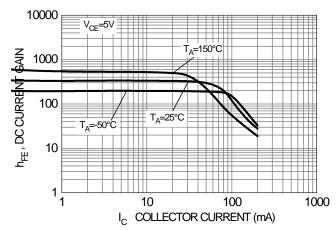
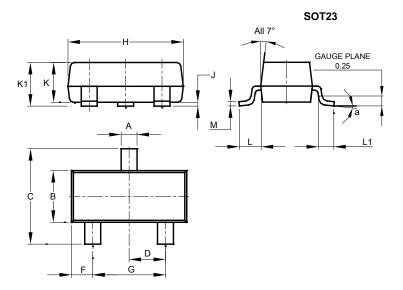


Figure 4 Typical DC Current Gain vs. Collector Current (Band B Group Gain)



Package Outline Dimensions

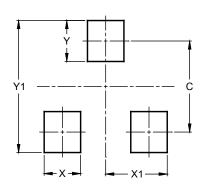
Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
М	0.085	0.150	0.110				
а	0°	8°					
All	Dimens	ions in	mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT23

Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9



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